

Abstract

Described are methods of processing one or more semiconductor wafers wherein the one or more wafers are processed in the presence of a gaseous antistatic agent. The method generally comprises performing one or more chemical treatment, rinsing, and/or drying steps in the presence of a gaseous antistatic agent. Preferably, a gaseous antistatic agent is present during at least a portion of a drying step and more preferably, during at least a portion of both a rinsing step and a drying step. In one preferred embodiment, the gaseous antistatic agent comprises carbon dioxide.

10 KJH/6812